

ABSTRACT

5 The present invention provides a sintered aluminum nitride body and a ceramic substrate, which show a volume resistivity of not less than $10^8 \Omega \cdot \text{cm}$ even at an elevated temperature of as high as 500°C .

10 The present invention relates to a ceramic substrate comprising a conductive layer disposed internally or on the surface thereof, wherein said ceramic substrate comprises a nitride ceramic and boron is contained in said nitride ceramic, and to a sintered aluminum nitride body containing boron.